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Serial No.: 10/044,493

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PATENT- AF
RESPONSE UNDER 37 C.F.R. 1.116
EXPEDITED PROCEDURE
EXAMINING GROUP 2826

CERTIFICATE OF MAILING (37 C.F.R. 1.8a)

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Bin Yu, et al.

Serial No.: 10/044,493

Art Unit: 2826

Filed: January 11, 2002

Confirmation No.: 9266

Title: SEMICONDUCTOR DEVICE WITH SILICIDE
SOURCE/DRAIN AND HIGH-K DIELECTRIC

Examiner: Kevin V. Quinto

Docket No.: G0615

RESPONSE UNDER 37 C.F.R. 1.116
TO OFFICE ACTION DATED DECEMBER 4, 2002

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Sir:

This reply is filed in response to the Office action dated December 4, 2002. It is believed that the reply raises no new issues, does not require an additional search and/or

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AGENT & TRA

U.S.F.R. 1.116
DECEMBER 4, 2002

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A marked version of the amended claim appears below (deletions bracketed and struck through and additions underlined):

20. (amended) A ~~[The]~~ semiconductor device ~~[according to claim 1,]~~
comprising:

a source and a drain, said source and drain consisting essentially of silicide;
a semiconductor body disposed between the source and the drain, wherein a
source/body junction is defined by silicide material of the source and semiconductor
material of the body and a drain/body junction is defined by silicide material of the drain
and semiconductor material of the body;
a gate electrode disposed over the body and defining a channel interposed
between the source and the drain; and
a gate dielectric made from a high-K material and separating the gate electrode
and the body.
